

CORRECTION

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Correction: Solution-processable Li-doped transition metal oxide hole-injection layer for highly efficient quantum-dot light-emitting diodes

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Correction for 'Solution-processable Li-doped transition metal oxide hole-injection layer for highly efficient quantum-dot light-emitting diodes' by Jae Seung Shin *et al.*, *J. Mater. Chem. C*, 2022, **10**, 5590–5597, <https://doi.org/10.1039/D1TC06117H>.

The authors regret that one of the authors' names (Hui Ung Hwang) was spelled incorrectly in the originally published article. The correct spelling is as shown above.

The Royal Society of Chemistry apologises for these errors and any consequent inconvenience to authors and readers.

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